

Application No. 09/768,912
Amendment dated: March 22, 2004
Reply to Final Office Action of February 13, 2004

IN THE CLAIMS

1 - 8. (Canceled)

9. (Currently amended) A semiconductor device comprising:
~~a single-crystal substrate made of a material different from nitride III-V compound semiconductors, and, said substrate extending between a first surface and a second surface opposite said first surface and having a hole extending through the substrate from said first surface to said second surface;~~
~~a device formed on one major surface of said first and second surfaces of said single-crystal substrate by using III-V compound semiconductors[.];~~
~~a layer disposed on said major surface one of said first and second surfaces of said single-crystal substrate and in electrical connection with said device; and;~~
~~wherein said device is formed between said layer and said substrate and is electrically connected to said layer; and~~
~~a via hole formed in said single-crystal substrate through to said layer;~~
~~wherein an electrical connection to said device is created through said via the hole extending through the substrate and contact with said layer.~~

10. (Currently amended) The semiconductor device according to claim 9, wherein said single-crystal substrate is ~~one of a~~comprises a material selected from a group consisting of sapphire substrate, spinel substrate, perovskite yttrium aluminite substrate and SiC substrate.

11. (Currently amended) The semiconductor device according to claim 9, wherein said semiconductor device ~~is~~comprises a semiconductor laser using nitride III-V compound semiconductors.

12. (Currently amended) The semiconductor device according to claim 9, wherein said semiconductor device ~~is~~comprises an FET using nitride III-V compound semiconductors.

Application No. 09/768,912
Amendment dated: March 22, 2004
Reply to Final Office Action of February 13, 2004

13 - 24. (Canceled)

25. (New) A semiconductor device comprising:

a single-crystal substrate made of a material different from nitride III-V compound semiconductors, said substrate extending between a first surface and a second surface opposite said first surface and having a hole extending through the substrate from said first surface to said second surface;

a device formed on one of said first and second surfaces of said single-crystal substrate using III-V compound semiconductors;

a layer disposed on one of said first and second surfaces of said single-crystal substrate and electrically connected to said device;

wherein a surface of the layer is at least as close to the substrate as a surface of the device facing the substrate; and

wherein an electrical connection to said device is created via the hole extending through the substrate and contact with said layer.